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Douglas J. Resnick
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Douglas J. Resnick, Molecular Imprints, Inc. (United States)
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John G. Maltabes, Hewlett-Packard Laboratories (United States)
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
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Hans Loeschner, IMS Nanofabrication AG (Austria)
Shy-Jay Lin, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)
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Christopher Bencher, Applied Materials, Inc. (United States)
- 8 Directed Self-Assembly III: Patterning
Benjamin M. Rathsack, Tokyo Electron America, Inc. (United States)
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